



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **Fumikazu YAMAKI et al.**

2826
#4/A
11/20/02
Mullish

Serial No.: **10/035,444**

Group Art Unit: **2826**

Filed: **January 4, 2002**

Examiner: **Tan N. Tran**

P.T.O. Confirmation No.: **3015**

For: **SEMICONDUCTOR DEVICE WITH A SUPER LATTICE BUFFER**

AMENDMENT UNDER 37 CFR §1.111

Commissioner for Patents
Washington, D.C. 20231

November 14, 2002

Sir:

In response to the Office Action dated **August 14, 2002**, please amend the above-identified application as follows:

CLEAN VERSION OF AMENDMENTS

IN THE CLAIMS:

Please amend claims 8 and 11 as follows:

Sub B27
A1

8. (Amended) A semiconductor device as claimed in claim 7, wherein the active layer has 2-Dimensional Electron Gasses.

A2

11. (Amended) A semiconductor device as claimed in claim 1, wherein the compound semiconductor substrate comprises a compound semiconductor support substrate having a resistivity more than 1.0×10^8 Ohm-cm and a compound semiconductor having a resistivity less than 1.0×10^8 Ohm-cm.

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